

## PUMH1-Q

# NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

14 November 2022

Product data sheet

## 1. General description

NPN/NPN Resistor-Equipped double Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replaces general-purpose transistors in digital applications

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	

[1] See section "Test information" for resistor calculation and test conditions.



#### NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

## 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3	
			TSSOP6 (SOT363)	<del></del>
				GND1 I1 O2 aaa-019894

## 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		
	Name	Description	Version
PUMH1-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>

## 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMH1-Q	Н%2

[1] % = placeholder for manufacturing site code

#### NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

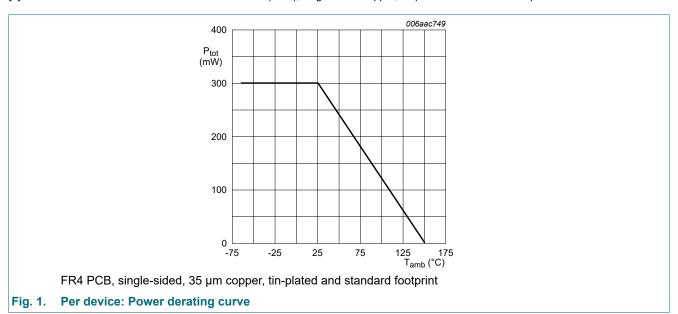
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or			'		
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-	40	V
		negative		-	-10	V
Io	output current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
Per device				'		'
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



#### NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

#### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or		,				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device			,				_
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

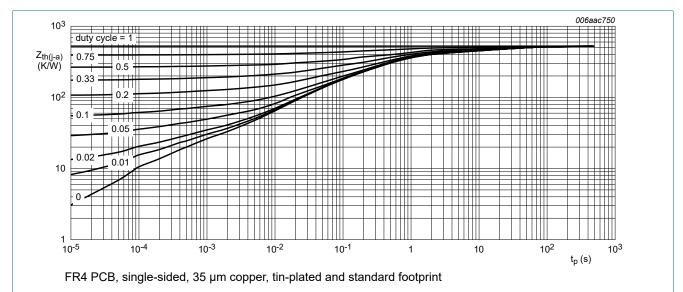


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### **Table 7. Characteristics**

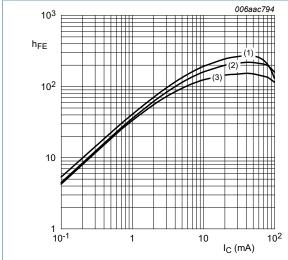
 $T_{amb}$  = 25°C unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
$V_{(BR)CBO}$	collector-base breakdown voltage	I <sub>C</sub> = 100 μA; I <sub>E</sub> = 0 A		50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage			50	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	I <sub>C</sub> = 0 A; I <sub>E</sub> = 100 A		10	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>CEO</sub> collector-emitter courrent	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	1	μΑ
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 150 °C		-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	180	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C		60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		-	1.1	0.8	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V; } I_{C} = 5 \text{ mA; } T_{amb} = 25 \text{ °C}$		2.5	1.7	-	V
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; f = 1 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	230	-	MHz

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[2]</sup> Characteristics of built-in transistor

#### NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

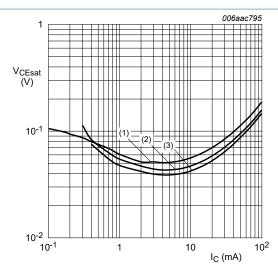


$$V_{CE} = 5 V$$

$$(1) T_{amb} = 100 ° ($$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 3. DC current gain as a function of collector current; typical values



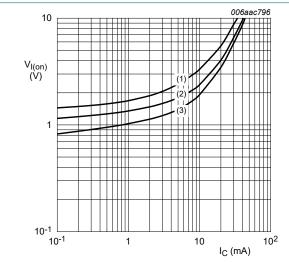
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_{C}/I_{B} = 20$$
(1)  $T_{amb} = 100 \, ^{\circ}C$ 
(2)  $T_{amb} = 25 \, ^{\circ}C$ 
(3)  $T_{amb} = -40 \, ^{\circ}C$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. Collector-emitter saturation voltage as a function of collector current; typical values

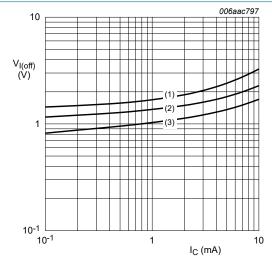


$$V_{CE}$$
 = 0.3  $V$ 

$$(1) T_{amb} = -40 ^{\circ} ($$

$$(3) T_{amb} = 100 °C$$

Fig. 5. On-state input voltage as a function of collector | Fig. 6. current; typical values



$$V_{CE}$$
 = 5  $V$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Off-state input voltage as a function of collector current; typical values

#### NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

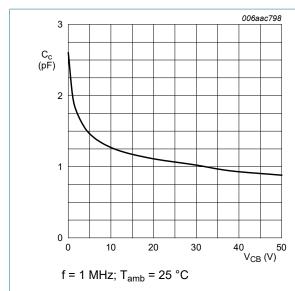


Fig. 7. Collector capacitance as a function of collectorbase voltage; typical values

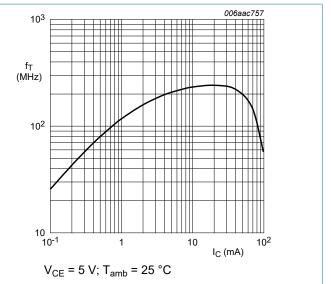


Fig. 8. Transition frequency as a function of collector current; typical values of built-in transistor

#### NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

#### 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

#### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

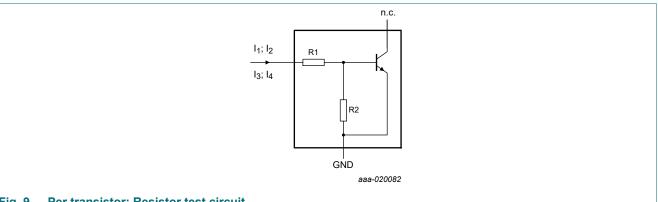


Fig. 9. Per transistor: Resistor test circuit

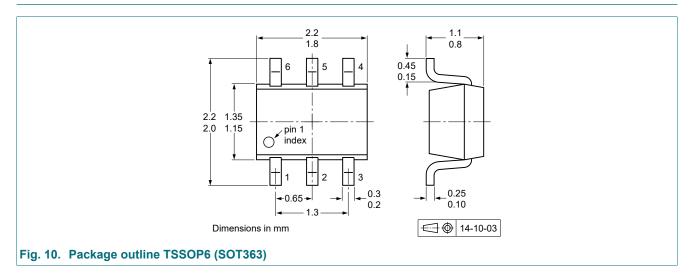
#### **Resistor test conditions**

**Table 8. Resistor test conditions** 

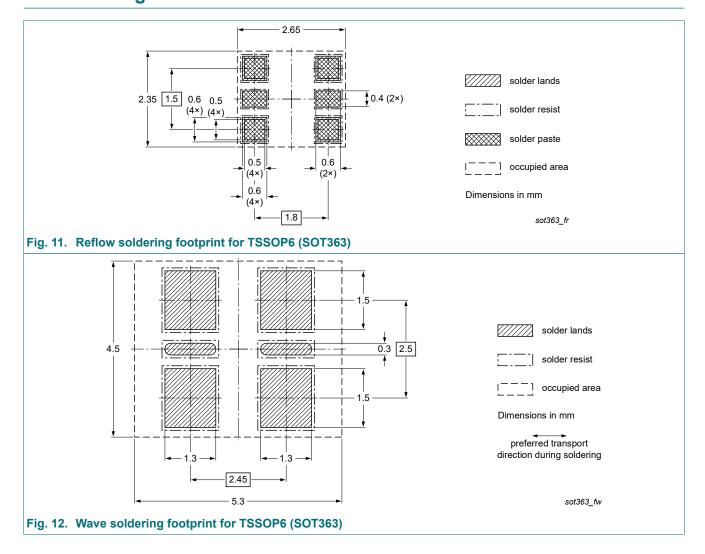
Type number	R1 (kΩ)	R2 (kΩ)	Test conditions	Test conditions			
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	I <sub>4</sub>	
PUMH1-Q	22	22	150 μΑ	230 μΑ	-150 μA	-230 μA	

NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

## 12. Package outline



## 13. Soldering



NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

## 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMH1-Q v.1	20221114	Product data sheet	-	-

#### NPN/NPN resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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#### **Contents**

1.	General description	1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	. 3
9.	Thermal characteristics	. 4
10.	Characteristics	5
11.	Test information	8
12.	Package outline	. 9
13.	Soldering	. 9
14.	Revision history	10
	Legal information	

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